LM3D65N03

LM N-Channel Super Trench Power MOSFET

Description

The LM3D65N03 uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g. This device is ideal for high-frequency switching and synchronous rectification.

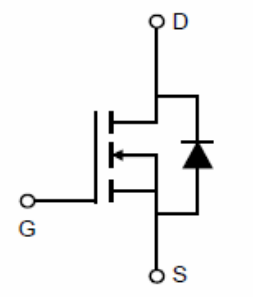
General Features

- V_{DS} =30V,I_D =65A
  $R_{DS(ON)}$=1.9mΩ (typical) @ V_{GS}=10V
  $R_{DS(ON)}$=3.0mΩ (typical) @ V_{GS}=4.5V
- Excellent gate charge x $R_{DS(on)}$ product(FOM)
- Very low on-resistance $R_{DS(on)}$
- 150 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

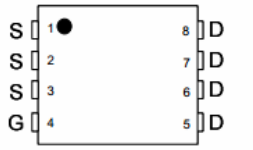
Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

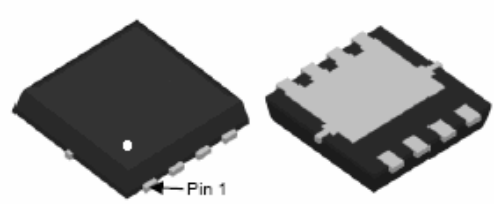
100% UIS TESTED!
100% ΔVds TESTED!



Schematic Diagram



Pin Assignment



Top View **Bottom View**

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP3065QU	LM3D65N03	DFN3.3X3.3-8L	-	-	-

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous	I_D	65	A
Drain Current-Continuous(T_C=100℃)	I_D (100℃)	45.5	A
Pulsed Drain Current	I_{DM}	260	A
Maximum Power Dissipation	P_D	55	W
Derating factor		0.44	W/℃
Single pulse avalanche energy (Note 5)	E_{AS}	500	mJ
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55 To 150	℃

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Thermal Characteristic

Thermal Resistance,Junction-to-Case (Note 2)	$R_{\theta JC}$	2.3	℃/W

Electrical Characteristics (T_C=25℃unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	30		-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=30V,V_{GS}=0V	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250μA	1.0	1.5	2.0	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=20A	-	1.9	2.3	mΩ
		V_{GS}=4.5V, I_D=20A	-	3.0	3.6	mΩ
Forward Transconductance	g_{FS}	V_{DS}=5V,I_D=20A		60	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{lss}	V_{DS}=15V,V_{GS}=0V, F=1.0MHz	-	2100	-	PF
Output Capacitance	C_{oss}		-	773	-	PF
Reverse Transfer Capacitance	C_{rss}		-	15.5	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=15V,I_D=20A V_{GS}=10V,R_G=1.6Ω	-	7.5	-	nS
Turn-on Rise Time	t_r		-	4.0	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	37	-	nS
Turn-Off Fall Time	t_f		-	7.5	-	nS
Total Gate Charge	Q_g	V_{DS}=15V,I_D=20A, V_{GS}=10V	-	34.8	-	nC
Gate-Source Charge	Q_{gs}		-	6.2		nC
Gate-Drain Charge	Q_{gd}		-	5.1		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V,I_S=20A	-		1.2	V
Diode Forward Current (Note 2)	I_S		-	-	65	A
Reverse Recovery Time	t_{rr}	T_J = 25°C, I_F = I_S di/dt = 100A/μs (Note3)	-	14	-	nS
Reverse Recovery Charge	Qrr		-	21	-	nC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production
5. EAS condition : Tj=25℃,V_{DD}=20V,V_G=10V,L=0.5mH,Rg=25Ω

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Typical Electrical and Thermal Characteristics

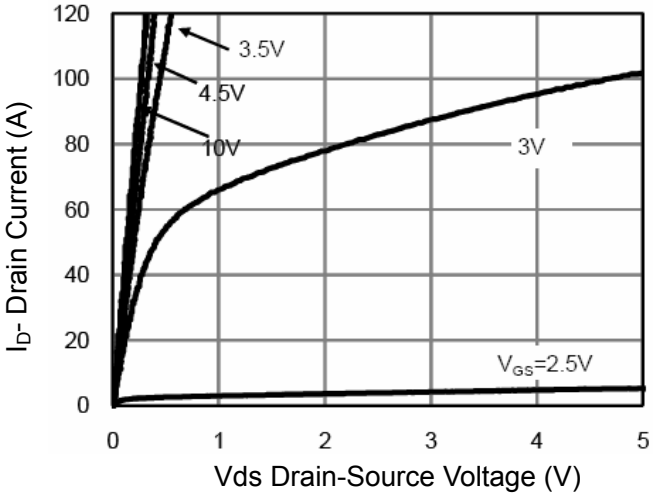


Figure 1 Output Characteristics

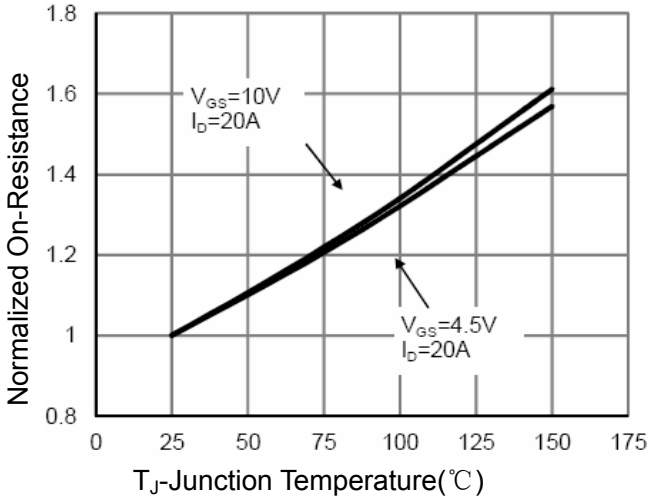


Figure 4 Rdson-Junction Temperature

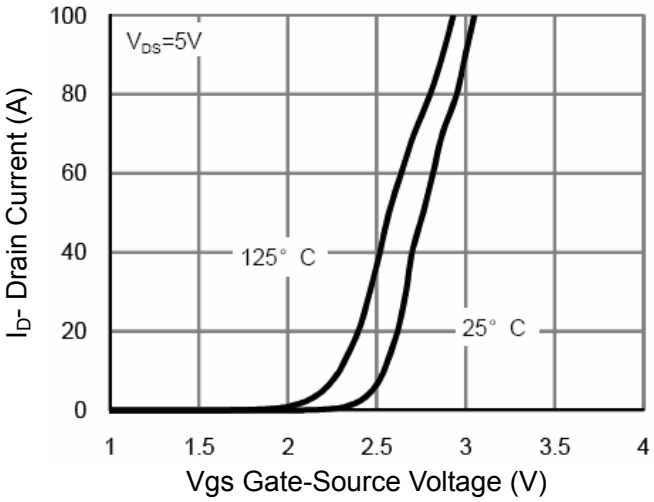


Figure 2 Transfer Characteristics

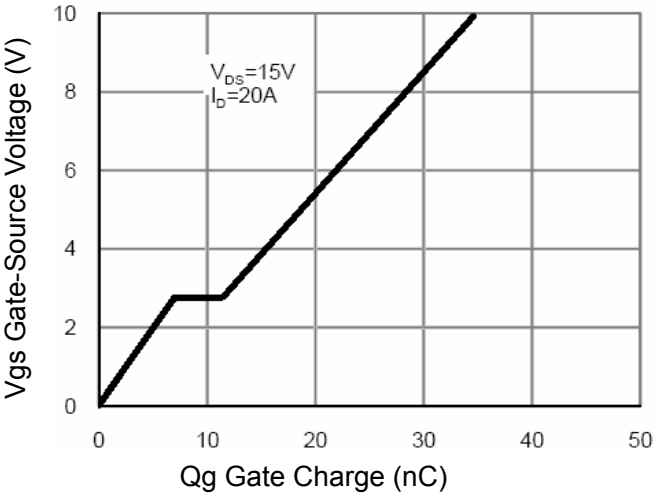


Figure 5 Gate Charge

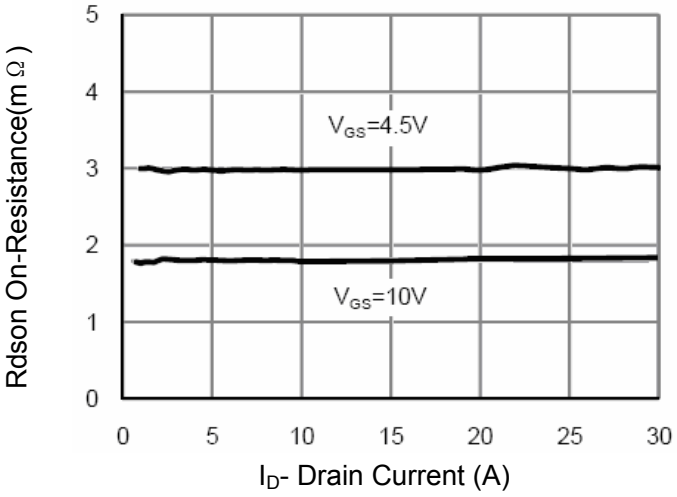


Figure 3 Rdson- Drain Current

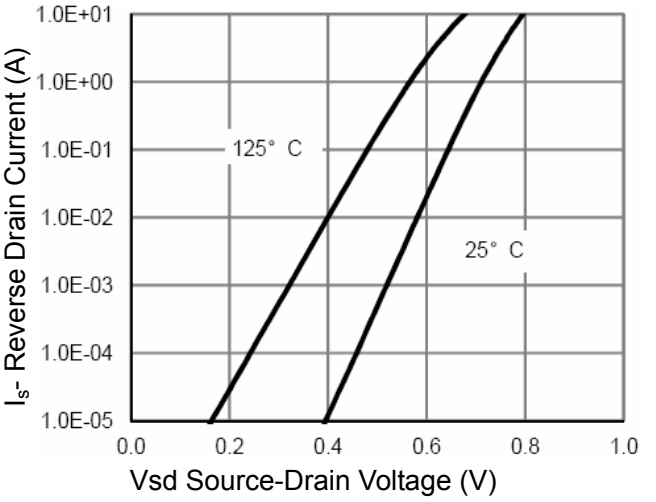


Figure 6 Source- Drain Diode Forward

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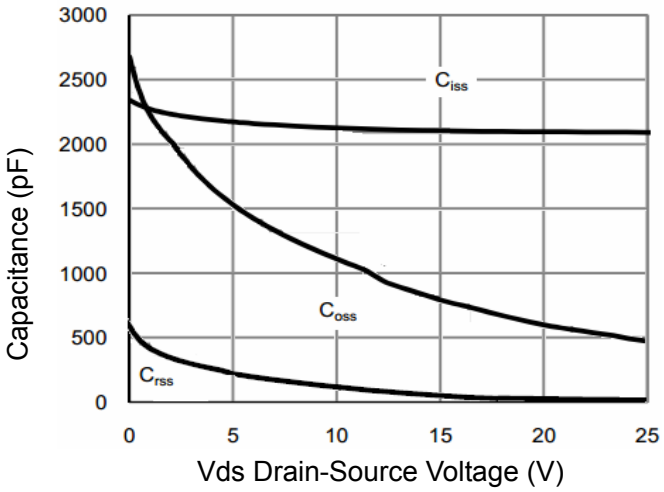


Figure 7 Capacitance vs Vds

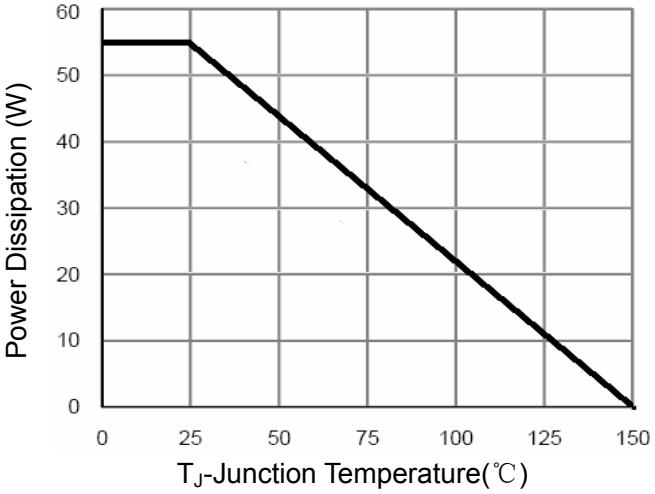


Figure 9 Power De-rating

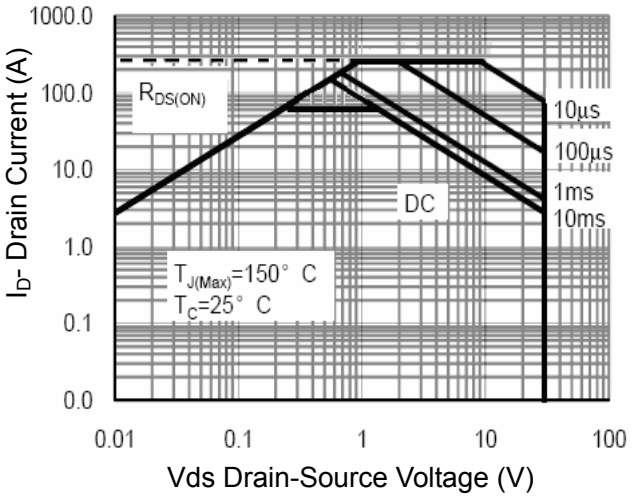


Figure 8 Safe Operation Area

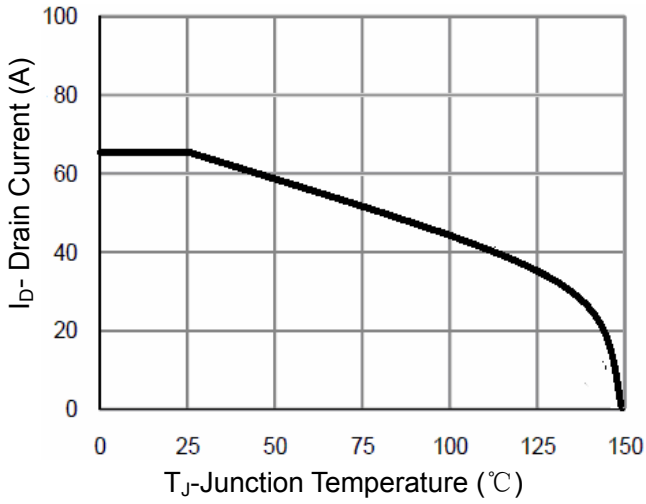


Figure 10 Current De-rating

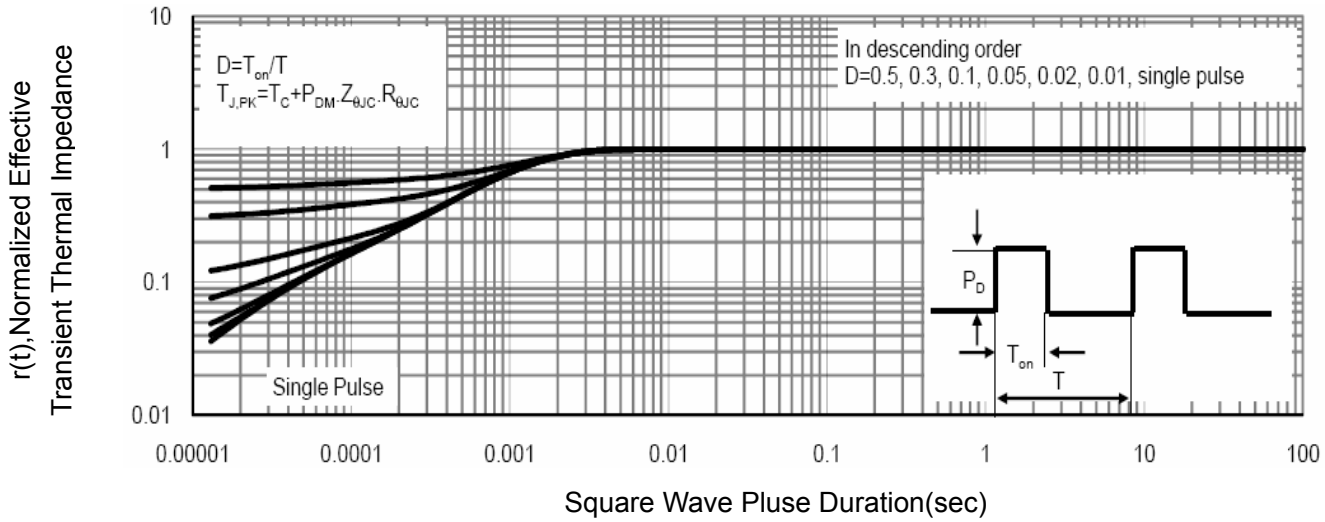
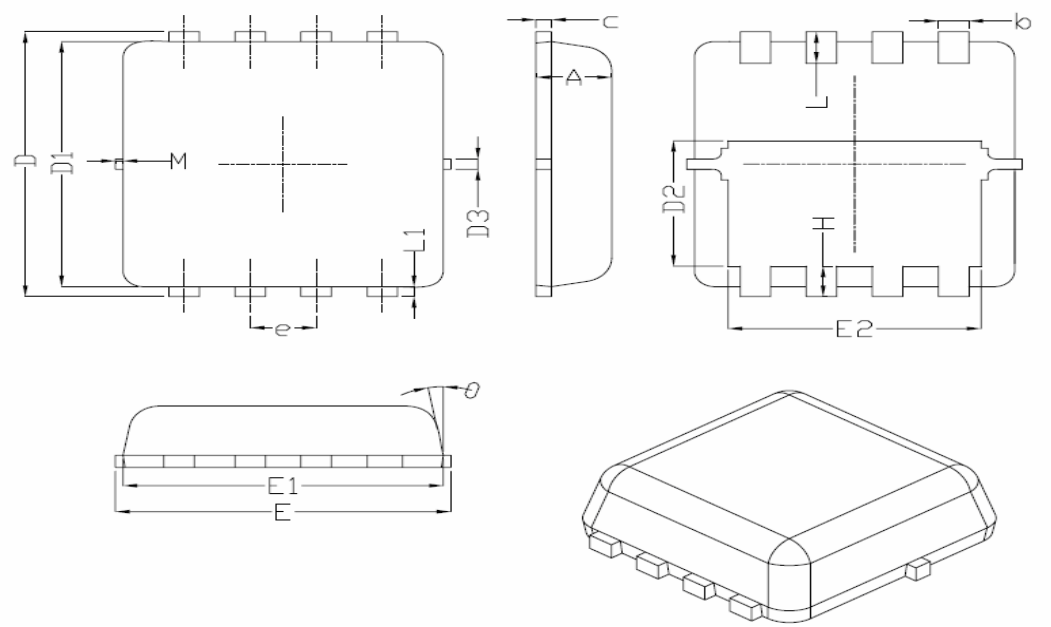


Figure 11 Normalized Maximum Transient Thermal Impedance

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DFN3.3X3.3-8L Package Information



Symbol	Dimensions In Millimeters		
	Min.	Nom.	Max.
A	0.70	0.75	0.80
b	0.25	0.30	0.35
c	0.10	0.15	0.25
D	3.25	3.35	3.45
D1	3.00	3.10	3.20
D2	1.48	1.58	1.68
D3	-	0.13	-
E	3.20	3.30	3.40
E1	3.00	3.15	3.20
E2	2.39	2.49	2.59
e	0.65BSC		
H	0.30	0.39	0.50
L	0.30	0.40	0.50
L1	-	0.13	-
M	*	*	0.15
θ		10°	12°

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